

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
20V	22mΩ@4.5V	6.8A
	30mΩ@2.5V	

Feature

- Advanced trench technology
- Excellent $R_{DS(on)}$
- Low gate charge
- ESD protected

Application

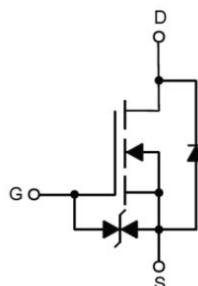
- Lithium battery protection
- Wireless impact
- Mobile phone fast charging

Package

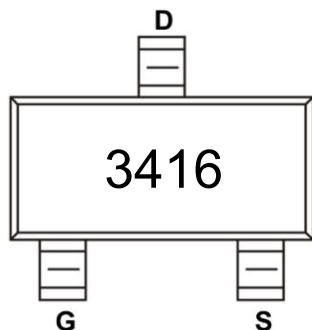


SOT-23

Circuit diagram



Marking



Absolute maximum ratings (T_c=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	20	V
Gate-Source Voltage	V _{GS}	±12	V
Continuous Drain Current ¹⁾ (T _A =25°C)	I _D	6.8	A
Continuous Drain Current ¹⁾ (T _A =70°C)	I _D (70°C)	6	A
Pulsed Drain Current ²⁾	I _{DM}	30	A
Power Dissipation ³⁾ (T _A =25°C)	P _D	1.5	W
Thermal Resistance Junction to Ambient ¹⁾	R _{θJA}	85	°C/W
Operating Junction Temperature	T _J	-55 ~ +150	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C

Electrical characteristics (T_c=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250μA	20			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =20V, V _{GS} =0V			1	μA
Gate-body leakage current	I _{GSS}	V _{DS} =0V, V _{GS} =±10V			±10	μA
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.5	0.65	1.2	V
Drain-source on-resistance	R _{DS(on)}	V _{GS} =4.5V, I _D =4A		15	22	mΩ
		V _{GS} =2.5V, I _D =3A		20	30	
Dynamic characteristics ⁴⁾						
Input Capacitance	C _{iss}	V _{DS} =10V, V _{GS} =0V, f =1MHz		780		pF
Output Capacitance	C _{oss}			140		
Reverse Transfer Capacitance	C _{rss}			80		
Total Gate Charge	Q _g	V _{DS} =10V, V _{GS} =4.5V, I _D =6.8A		11		nC
Gate-Source Charge	Q _{gs}			2.3		
Gate-Drain Charge	Q _{gd}			2.9		
Turn-on delay time	t _{d(on)}	V _{DS} =10V, V _{GS} =4.5V, I _D =6.8A R _G =3Ω		9		nS
Turn-on rise time	t _r			30		
Turn-off delay time	t _{d(off)}			35		
Turn-off fall time	t _f			10		
Source-Drain Diode characteristics						
Diode Forward Current	I _S				6.8	A
Diode Forward voltage	V _{SD}	V _{GS} =0V, I _S =6.8A			1.2	V

Notes:

- 1) The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2) The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
- 3) The power dissipation is limited by 150°C junction temperature.
- 4) Guaranteed by design, not subject to production testing.

Typical Characteristics

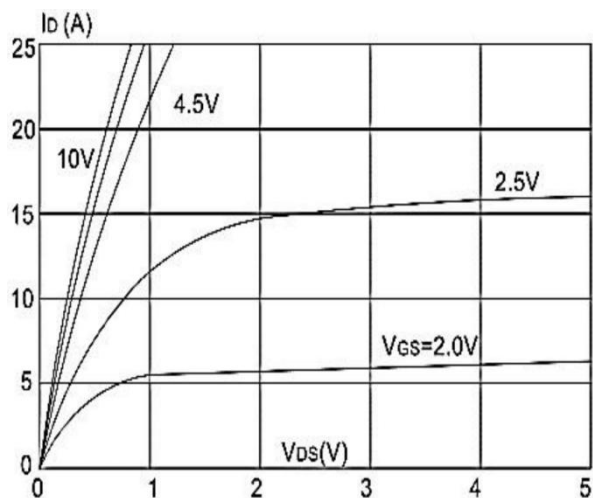


Figure1: Output Characteristics

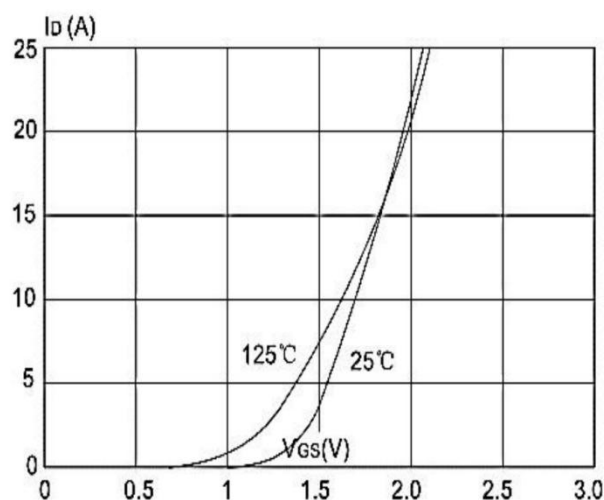


Figure 2: Typical Transfer Characteristics

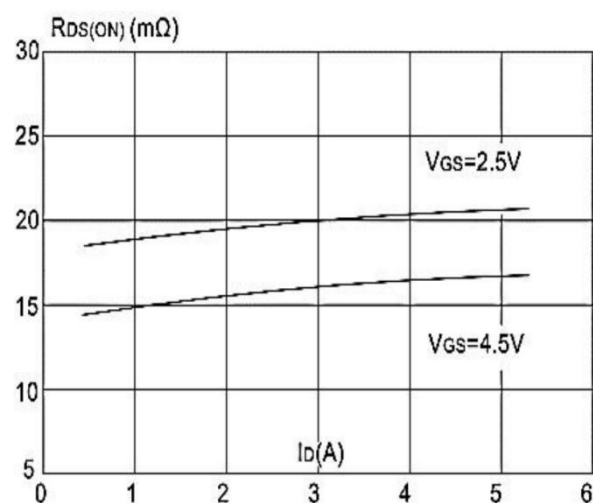


Figure 3: On-resistance vs. Drain Current

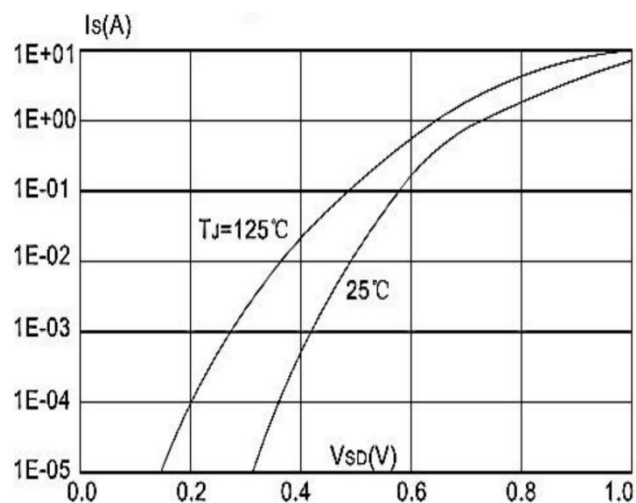


Figure 4: Body Diode Characteristics

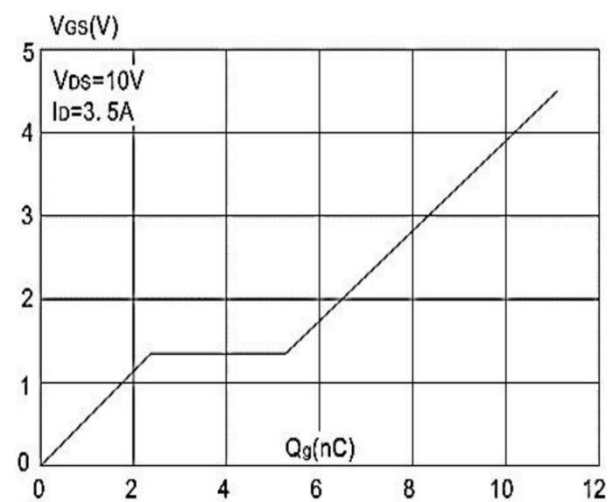


Figure 5: Gate Charge Characteristics

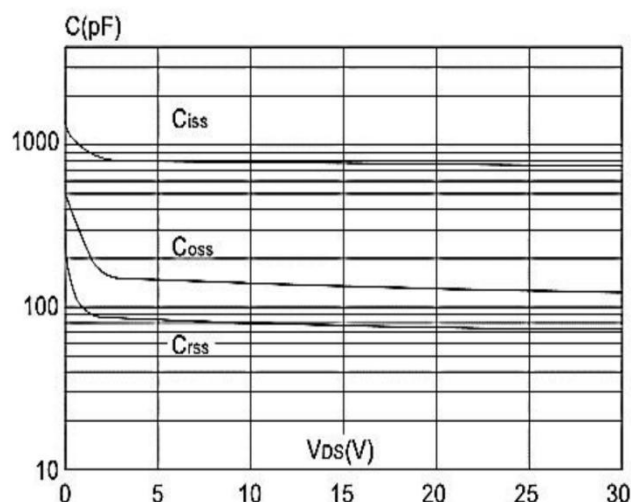


Figure 6: Capacitance Characteristics

Typical Characteristics

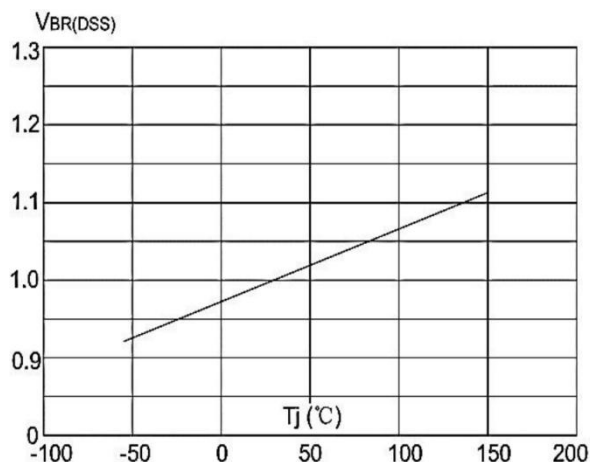


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

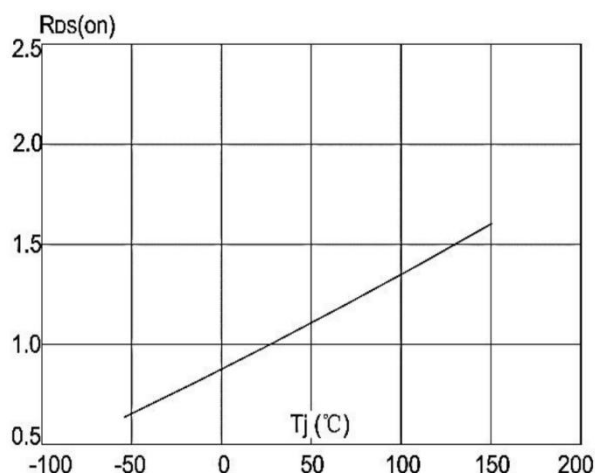


Figure 8: Normalized on Resistance vs. Junction Temperature

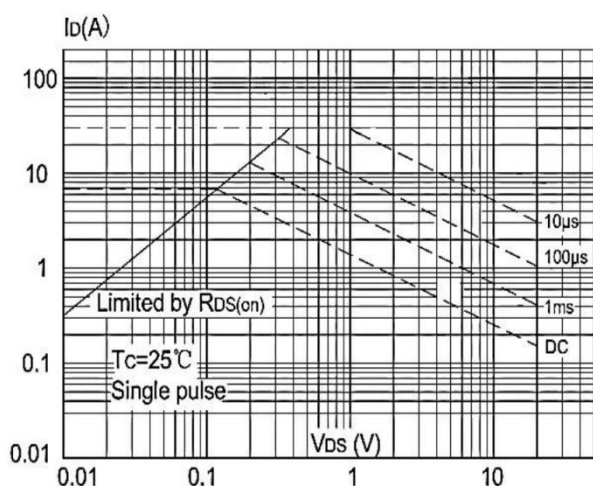


Figure 9: Maximum Safe Operating Area

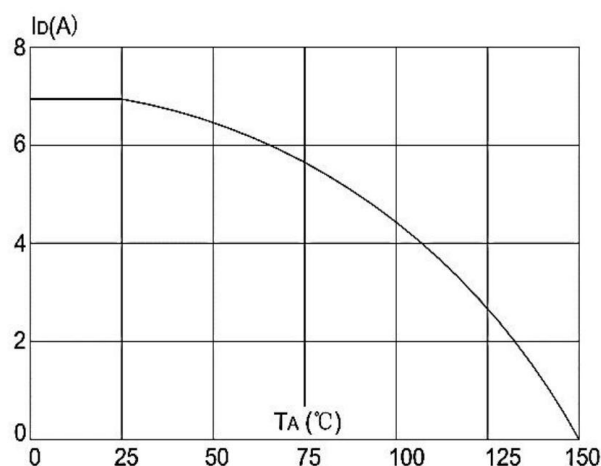


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

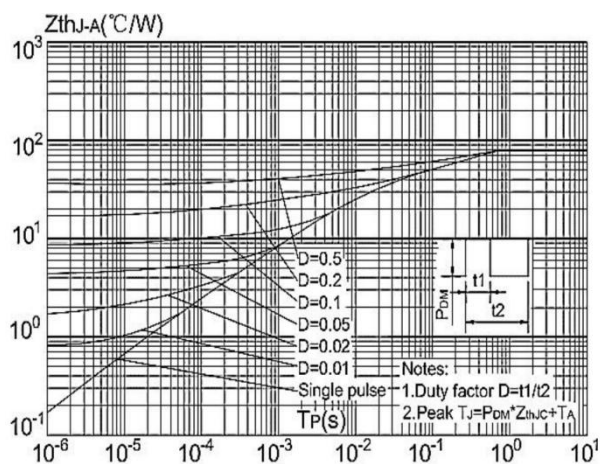
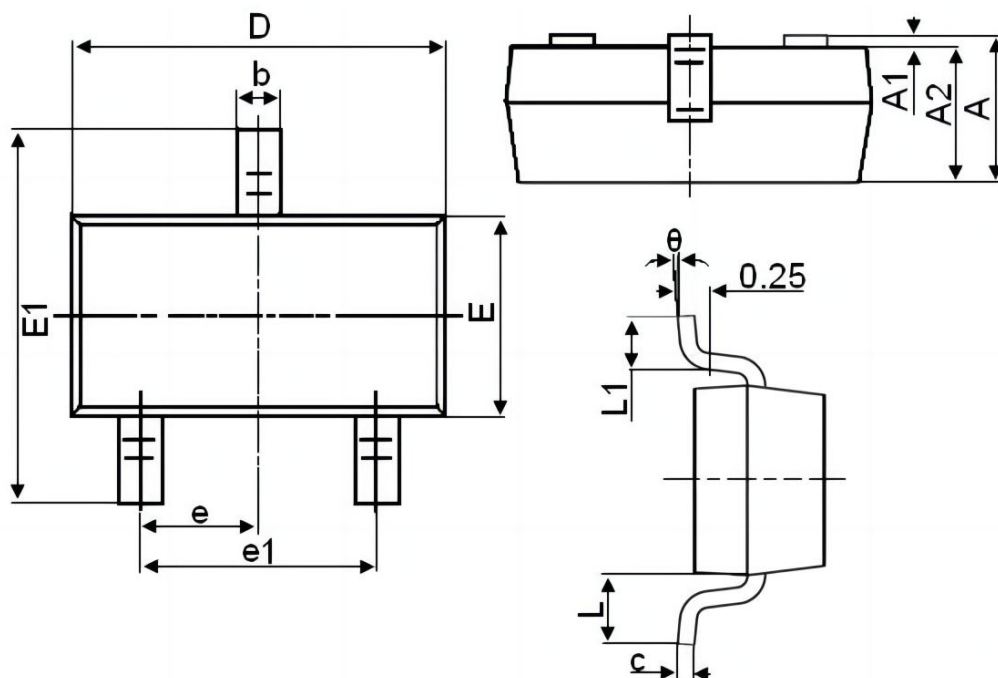


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case

SOT-23 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
C	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°